



#### 32V PNP MEDIUM POWER TRANSISTOR IN TO252

#### **Features**

- BVceo > -32V
- Ic = -2A High Continuous Collector Current
- I<sub>CM</sub> = -3A Peak Pulse Current
- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Medium Power Switching or Amplification Applications
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The 2DB1182Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

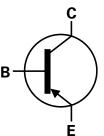
### **Mechanical Data**

- Package: TO252
- Package Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Weight: 0.34 grams (Approximate)

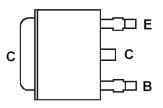




Top View



Device Schematic



Pinout Configuration Top view

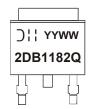
#### **Ordering Information** (Note 4)

Orderable Part Number	Package	Marking	Marking Book Size (inches) Tone Midth (mm)	Tape Width (mm)	Packing		
Orderable Part Number	ber Package Marking Reel S		Reel Size (inches)	rape width (IIIII)	Qty.	Carrier	
2DB1182Q-13	TO252 (DPAK)	2DB1182Q	13	16	3,000	Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**



2DB1182Q = Product Type Marking Code

Old = Manufacturer's Code Marking

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 25 = 2025)

WW = Week Code (01 to 52)



# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	Vсво	-40	V
Collector-Emitter Voltage	VCEO	-32	V
Emitter-Base Voltage	VEBO	-5	V
Continuous Collector Current	Ic	-2	Α
Peak Pulse Collector Current	Ісм	-3	Α

#### Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	PD	1.2	W
Power Dissipation @T <sub>L</sub> = +25°C	(Note 6)	PD	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)		R <sub>θJA</sub>	104	°C/W
Thermal Resistance, Junction to Lead (Note 7)		Rejl	8.3	°C/W
Thermal Resistance, Junction to Case (Note 5)		Rejc	18	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C	

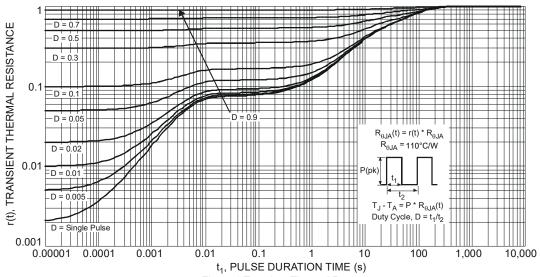
### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

- 5. For a device mounted with the exposed collector pad on minimum recommended pad (MRP) layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady state.
- 6. Same as Note 5 except the device is mounted on 15mm  $\times$  15mm 1oz copper.
- 7. Thermal resistance from junction to solder-point at the end of the collector lead .
- 8. Refer to JEDEC specifications JESD22-A114 and JESD22-A115.

#### **Thermal Characteristics**





## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)							
Collector-Base Breakdown Voltage	ВУсво	-40	_		V	I <sub>C</sub> = -50μA, I <sub>E</sub> = 0	
Collector-Emitter Breakdown Voltage	BVceo	-32	_	_	V	$I_C = -1mA$ , $I_B = 0$	
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-5	_	_	V	$I_E = -50\mu A$ , $I_C = 0$	
Collector Cutoff Current	Ісво		_	-1	μA	V <sub>CB</sub> = -20V, I <sub>E</sub> = 0	
Emitter Cutoff Current	IEBO		_	-1	μA	$V_{EB} = -4V, I_{C} = 0$	
ON CHARACTERISTICS (Note 9)							
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>		_	-0.8	V	$I_C = -2A$ , $I_B = -0.2A$	
DC Current Gain	hFE	120	_	270	_	$V_{CE} = -3V$ , $I_{C} = -0.5A$	
SMALL-SIGNAL CHARACTERISTICS							
Current Gain-Bandwidth Product	f⊤		110	_	MHz	V <sub>CE</sub> = -5V, I <sub>C</sub> = -0.1A f = 30MHz	
Output Capacitance	Cobo	_	26	_	pF	V <sub>CB</sub> = -10V, f = 1MHz	
Turn-On Time	ton		109	_	ns		
Delay Time	td		60	_	ns	]	
Rise Time	t <sub>r</sub>	_	49	_	ns	Vcc = 30V Icc = 150mA I <sub>B1</sub> = -I <sub>B2</sub> = 15mA	
Turn-Off Time	toff	_	280	_	ns		
Storage Time	ts		246		ns	אוווא בטו וטו	
Fall Time	tf	_	34	_	ns		

Note: 9. Measured under pulsed conditions. Pulse width =  $300\mu$ s. Duty cycle  $\leq 2\%$ .



# $\textbf{Typical Electrical Characteristics} \ ( \textcircled{@} T_{A} = +25 ^{\circ} C, \ unless \ otherwise \ specified. )$

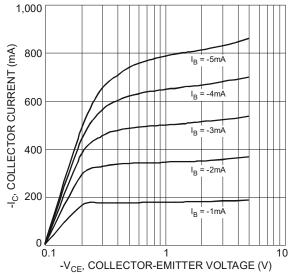


Figure 2 Typical Collector Current vs. Collector-Emitter Voltage

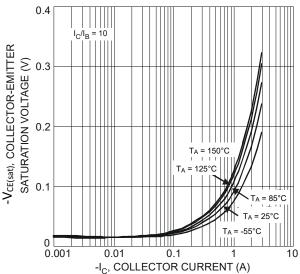


Figure 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

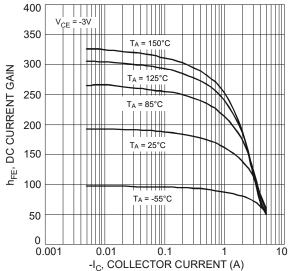


Figure 3 Typical DC Current Gain vs. Collector Current

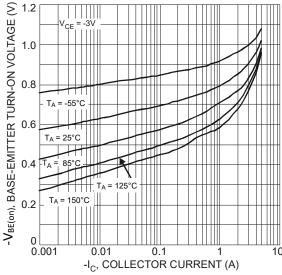


Figure 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current



### Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.) (continued)

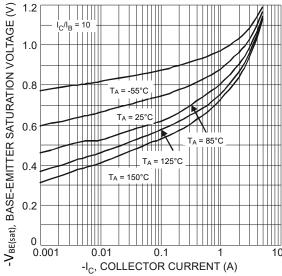
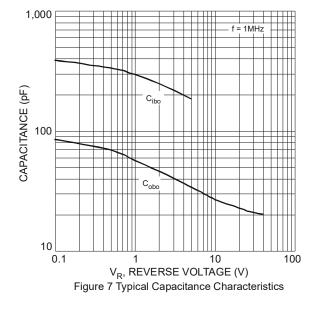


Figure 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



140 f<sub>T</sub>, GAIN-BANDWIDTH PRODUCT (MHz) 120 V<sub>CE</sub> = -5V f = 30MHz 100 80 60 40 20 10 90 100 30 40 50 60 70 80 I<sub>C</sub>, COLLECTOR CURRENT (mA)

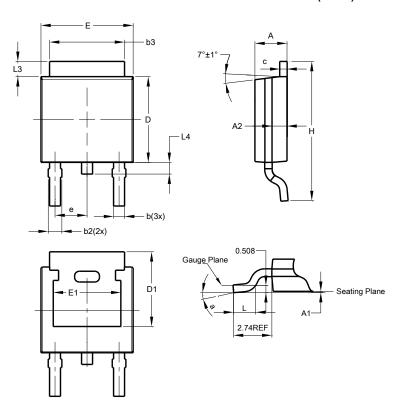
Figure 8 Typical Gain-Bandwidth Product vs. Collector Current



### **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO252 (DPAK)

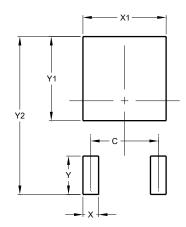


TO252 (DPAK)					
Dim	Min	Max	Тур		
Α	2.19	2.39	2.29		
<b>A1</b>	0.00	0.13	0.08		
<b>A2</b>	0.97	1.17	1.07		
b	0.64	0.88	0.783		
b2	0.76	1.14	0.95		
b3	5.21	5.50	5.33		
O	0.45	0.58	0.531		
D	6.00	6.20	6.10		
D1	5.21				
е	2.	286 BS	S		
П	6.45	6.70	6.58		
E1	4.32	-			
H	9.40	10.41	9.91		
٦	1.40	1.78	1.59		
L3	0.88	1.27	1.08		
L4	0.64	1.02	0.83		
а	0°	10°			
All Dimensions in mm					

### **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### TO252 (DPAK)



Dimensions	Value (in mm)
С	4.572
Х	1.060
X1	5.632
Υ	2.600
Y1	5.700
Y2	10 700



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